Method of Fabricating a Poly-Poly Capacitor With A SiGe BiCMOS Integration Scheme

ABSTRACT OF THE DISCLOSURE

A method for fabricating a poly-poly capacitor integrated with a BiCMOS process which includes forming a lower plate electrode (22) of a poly-poly capacitor during deposition of a gate electrode of a CMOS transistor; and forming an upper SiGe plate electrode during growth of a SiGe base region of a heterojunction bipolar transistor.

FIG 6.